

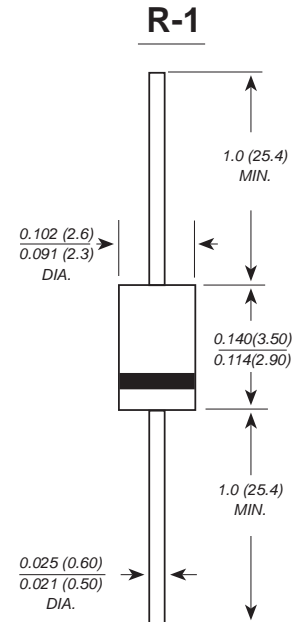
**VOLTAGE RANGE: 30 - 100V**  
**CURRENT: 1.0 A**

### Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

### Mechanical Data

- Case: R-1 molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750,
- Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.007 ounce, 0.20 grams



Dimensions in inches and (millimeters)

### Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	11EQS03	11EQS04	11EQS06	11EQS10	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$	30	40	60	100	V
Working Peak Reverse Voltage	$V_{RWM}$					
DC Blocking Voltage	$V_R$					
RMS Reverse Voltage	$V_{R(RMS)}$	21	28	42	70	V
Average Rectified Output Current @ $T_L = 100^\circ\text{C}$ (Note 1)	$I_o$	1.0				A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	40				A
Forward Voltage @ $I_F = 1.0\text{A}$	$V_{FM}$	0.50		0.70	0.85	V
Peak Reverse Current @ $T_A = 25^\circ\text{C}$	$I_{RM}$	0.5				mA
At Rated DC Blocking Voltage @ $T_A = 100^\circ\text{C}$		10				
Typical Junction Capacitance (Note 2)	$C_j$	110		80		pF
Typical Thermal Resistance (Note 1)	$R_{\theta JL}$ $R_{\theta JA}$	15 50				$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_j, T_{STG}$	-65 to +150				$^\circ\text{C}$

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.  
 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

## RATINGS AND CHARACTERISTIC CURVES 11EQS03 THRU 11EQS10

